NST847BF3T5G

NPN General Purpose Transistor

The NST847BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 200-450
- Low $V_{CE(sat)}$, $\leq 0.25 \text{ V}$
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	Vdc
Collector - Base Voltage	V _{CBO}	50	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	I _C	100	mAdc

THERMAL CHARACTERISTICS

	1		
Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

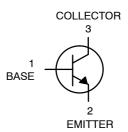
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm² 1 oz, copper traces.
- 2. 500 mm² 1 oz, copper traces.



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NST847BF3T5G



SOT-1123 CASE 524AA STYLE 1

MARKING DIAGRAM



4 = Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST847BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST847BF3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I _C = 10 mA)	V _{(BR)CEO}	45	-	-	V
Collector – Emitter Breakdown Voltage (I _C = 10 μA, V _{EB} = 0)	V _{(BR)CES}	50	-	-	V
Collector – Base Breakdown Voltage (I _C = 10 μA)	V _{(BR)CBO}	50	-	-	V
Emitter – Base Breakdown Voltage (I _E = 1.0 μA)	V _{(BR)EBO}	6.0	_	-	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	-	-	15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C=10~\mu\text{A},~V_{CE}=5.0~\text{V})\\ &(I_C=2.0~\text{mA},~V_{CE}=5.0~\text{V}) \end{aligned} $	h _{FE}	- 200	150 290	- 450	-
Collector – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{CE(sat)}	-	-	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}	- -	0.7 0.9	-	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)	V _{BE(on)}	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	100	-	-	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Input Capacitance (V _{EB} = 0.5 V, I _C = 0 mA, f = 1.0 MHz)	C _{ibo}	-	-	10	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	_	-	10	dB

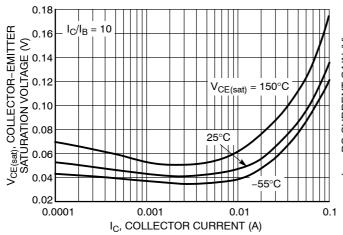


Figure 1. Collector Emitter Saturation Voltage vs.
Collector Current

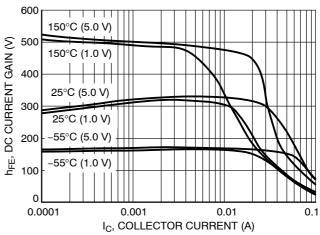


Figure 2. DC Current Gain vs. Collector Current

NST847BF3T5G

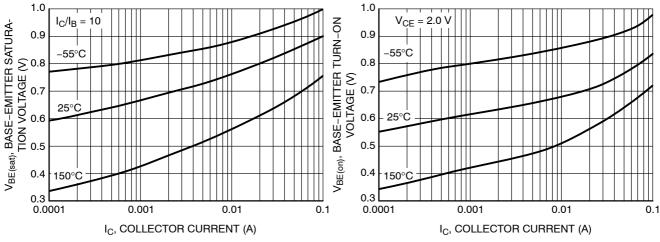


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

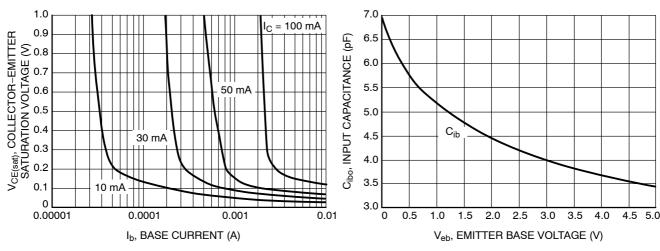


Figure 5. Saturation Region

Figure 6. Input Capacitance

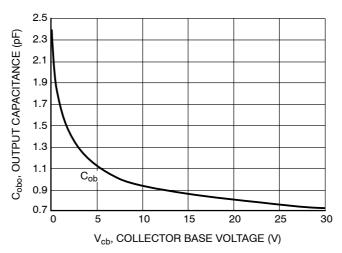


Figure 7. Output Capacitance

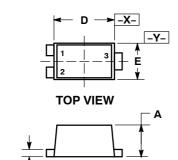




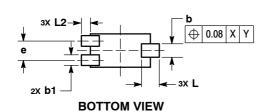
SOT-1123 CASE 524AA **ISSUE C**

DATE 29 NOV 2011

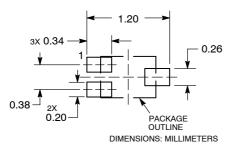
SCALE 8:1



HE SIDE VIEW



SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME
- DIMENSIONING AND TOLERANOR PER ASM Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
С	0.07	0.17		
D	0.75	0.85		
Ε	0.55	0.65		
е	0.35	0.40		
HE	0.95	1.05		
L	0.185 REF			
L2	0.05 0.15			

GENERIC MARKING DIAGRAM*



= Specific Device Code

= Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	CATHODE	2. SOURCE
COLLECTOR	CATHODE	CATHODE	ANODE	3. DRAIN

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P		PAGE 1 OF 1	

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